

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-2157		SERIAL NO. <del>Unknown</del> 10/288,748		
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT: Don Carl Powell				
				FILING DATE Filed Herewith 10/17/03		GROUP 2891 Unknown		
<b>U.S. PATENT DOCUMENTS</b>								
Examiner's Initials	AA	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate	
CME	AA	5,739,066	04/14/98	Pan	438	595	—	
CME	AB	6,114,735	09/05/00	Batra et al.	257	411	—	
CME	AC	6,335,254 B1	01/01/02	Trivedi	438	305	—	
	AD							
	AE							
	AF							
	AG							
	AH							
	AI							
<b>FOREIGN PATENT DOCUMENTS</b>								
		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AJ							
	AK							
	AL							
<b>OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)</b>								
CME	AM		Hiura et al., <i>Integration Technology of Polymetal (WWSiN/Poly-Si) Dual Gate CMOS for 1 Gbit DRAMs and Beyond</i> , IEEE 398-392 (September 1998).					
CME	AN		Kawada et al., <i>Water Vapor Generator by Catalytic Reactor</i> (pre-February 2001).					
CME	AO		Lee et al., <i>In-situ Barrier Formation for High Reliable W/barrier/poly-Si Gate Using Denudation of WN, on Polycrystalline Si</i> , IEEE 385-388 (September 1998).					
EXAMINER C. Evers		DATE CONSIDERED 4-27-05						
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Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-2157	SERIAL NO. <del>Unknown</del> <i>10/688,748</i>
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT: Don Carl Powell	
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U.S. PATENT DOCUMENTS							
Examiner's Initials	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate	
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	AB						
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FOREIGN PATENT DOCUMENTS							
Document Number	Date	Country	Class	Subclass	Translation		
					Yes	No	

  

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)		
<i>CME</i>	AM	Nagahama et al., <i>Wet Hydrogen Oxidation System for Metal gate LSI's</i> (pre-February 2001).
<i>CME</i>	AN	Ohnishi et al., <i>Improving gate oxide integrity (GOI) of a W/WNx/dual-poly Si stacked-gate by using Wet-Hydrogen oxidation in 0.14-<math>\mu</math>m CMOS devices</i> , IEEE 397-400 (September 1998).
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EXAMINER <i>C. Buckner</i>		DATE CONSIDERED <i>4-27-05</i>

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